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Sheet 1 of 4

FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

ATTY. DOCKET NO.

107317-00039

SERIAL NO

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J-971 U.S. PTO
10/028429

12/28/01

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EXAMINER INITIAL		DOCUMENT NO.	DATE	NAME	CLASS	SUB- CLASS	FILING DATE
K.N.	AA	4,563,367	1/7/86	SHERMAN	156	643	
K.N.	AB	4,564,997	1/21/86	MATSUO ET AL.	156	647	
K.N.	AC	5,016,564	5/21/91	NAKAMURA ET AL.	156	345	
K.N.	AD	4,960,073	10/2/90	SUZUKI ET AL.	156	345	
K.N.	AE	5,022,977	6/11/91	MATSUOKA ET AL.			
K.N.	AF	5,259,922	11/9/93	YAMMNO ET AL.	156	643	

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K.N.	AG	5-90224	4/9/93	JAPAN					
K.N.	AH	60/117723	6/25/85	JAPAN					
K.N.	AI	4-340717	11/27/92	JAPAN					
K.N.	AJ	2-94628	4/5/90	JAPAN	156	345			
K.N.	AK	1-14920	1/19/89	JAPAN	156	345			
K.N.	AL	1-32631	2/2/89	JAPAN	156	345			

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K.N.	AM	N. Jiwari et al., Japan J. Appl. Phys. 32(6b) 3019 "Al etching...helicon wave plasma", 6/1993.
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K.N.	AO	M.W. Horn et al., Optical Eng. 32(10) 2388 "Comparison of etching tools...", 10/1993.

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12/5/02

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K.N.	AB	5,156,703	10/20/92	OECHSNER	156	643	
K.N.	AC	5,183,777	2/2/93	DORI et al.	437	225	
K.N.	AD	5,444,207	8/22/95	SEKINE et al.	204	298	
K.N.	AE	5,290,382	3/1/94	ZAROWIN et al.	204	298	
K.N.	AF	4,298,419	11/3/81	SUZUKI et al.	216	70	

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K.N.	AG	04-354124	12/8/92	JAPAN					
K.N.	AH	5-234955	9/10/93	JAPAN	216	70			
K.N.	AI	63-43324	2/24/88	JAPAN	156	345			
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K.N.	AM	"Charging Damage to Gate Oxides in a O ₂ Magnetron Plasma", Fang et al., J. Appl. Phys., Vol. 72, No. 10, November 15, 1992, pgs 4865-4872.
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K.N.	AO	M. Shimada et al., J. Vac. Sci. Technol. A 11(11), July/August 1993, pg. 1313, "Compact ECR ion source with a permanent magnet".

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Khien Nguyen

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K.N.	AA	5,368,685	11/29/94	KUMIHASHI et al.	216	70	
K.N.	AB	4,971,651	11/20/90	WATANABE et al.	216	70	
K.N.	AC	5,350,710	9/27/94	HONG et al.	156	643	
K.N.	AD	5,378,311	1/3/95	NAGAYAMA et al.	156	643	
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K.N.	AM	K. Junck et al., J. Vac. Sci. Technol. A12(3), May/June 1994, pg760, "ECR plasmas in 3 magnetic field configurations"
K.N.	AN	V. Hashimoto, Japan J. Appl. Phys., 32 (1993) 6109, "Charge Damage in Plasma Etching...through Antenna".
K.N.	AO	S. Samukawa et al., J. Vac Sci. Technol, B93 (1991) 1471 "400 KMZ RF biased ECR plasma etching for"

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K.B. Cunningham

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K.N.	AM	S. Samukawa, Japan J. Appl. Phys. 30, 11B (1991) 3154 "400 KHZ RF biased ECR resonance position etching".
K.N.	AN	S. Wolf & R.N. Tauber, "Silicon processing for the ULSI era", Vol I, 1986, pg.581.
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